

Spectrally-shaped illumination for improved optical inspection of lateral III-V-semiconductor oxidation N. MONVOISIN¹, E. HEMSLEY¹, L. LAPLANCHE¹, G. ALMUNEAU¹, S. CALVEZ¹, A. MONMAYRANT¹ ¹LAAS-CNRS, Université de Toulouse, CNRS, 7 Avenue du Colonel Roche, 31400 Toulouse, France

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Shaped illumination spectrum

Inspection of buried oxide aperture in VCSEL* fabrication







Detected radius (orange line) in polar coordinate together with the confidence interval (orange area) and the average radius (black line)



Spectrally-shaped illumination :

- Improves the detection of the oxide/unoxide boundary. It combines the high flux and low noise from the panchromatic imaging with the high contrast from the monochromatic illumination.
- Is a versatile solution with regard to VCSEL spectral response : arbitrary tailored spectrum, temporal reconfigurability.
- Is compatible with real-time monitoring : embedded DMD system, synchronization DMD-camera, multiplexed reflectivity spectrum measurement (Hadamard).

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 Implementation of real-time monitoring. • More advanced illumination spectrum optimization techniques : Fisher Discriminant Analysis (FDA), Principle Component Analysis (PCA).

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